Title: THERMAL INTERMEDIATE APPARATUS, SYSTEMS, AND METHODS

Assignee: Intel Corporation

## IN THE CLAIMS

Please amend the claims as follows:

- 1-6. (Canceled)
- 7. (Currently Amended) An integrated circuit package, comprising
  - a die;
- a heat sink, wherein both an upper surface of the die and a lower surface of the heat sink have metal coatings of gold; and
- a first thermal intermediate portion comprising a plurality of carbon nanotubes, some nanotubes of which have organic moieties attached to one end thereof, the one end of some nanotubes chemically bonded to the heat sink; and
- a second thermal intermediate portion comprising a plurality of carbon nanotubes, some nanotubes of which have organic moieties attached to one end thereof, the one end of some nanotubes chemically bonded to the die.
- 8. (Currently Amended) The package of claim 7, wherein the organic moieties of the first thermal intermediate portion and the organic moieties of the second thermal intermediate layer portion include amide linkers.
- 9. (Currently Amended) The package of claim 7, wherein the organic moieties of the first intermediate potion and the organic moieties of the second intermediate <u>layer portion</u> include thiol linkers.
- 10. (Original) The package of claim 7, wherein the organic moieties of the first intermediate portion and the organic moieties of the second intermediate portion include thiol linkers and amide linkers.

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11. (Currently Amended) The package of claim 10, wherein the carbon nanotubes of the thermal intermediate portions are generally perpendicular to [[a]] the upper surface of the die or the lower surface of the heat sink.

12-16. (Canceled)

- 17. (Currently Amended) A computing system, comprising:
  - at least one dynamic random access memory device;
  - a die having a circuit thereon to couple to the memory device;
- a heat sink, wherein both an upper surface of the die and a lower surface of the heat sink have metal coatings of gold; [[and]]
- a first thermal intermediate portion comprising a plurality of carbon nanotubes, some nanotubes of which have organic moieties attached to one end thereof, the one end of some nanotubes chemically bonded to the heat sink; and
- a second thermal intermediate portion comprising a plurality of carbon nanotubes, some nanotubes of which have organic moieties attached to one end thereof, the one end of some nanotubes chemically bonded to the die.
- a thermal intermediate structure comprising a plurality of carbon nanotubes, some of which are have organic moieties attached to one end thereof to tether them to at least one of the die and the heat sink.
- 18. (Previously Presented) The system of claim 17, wherein the circuit comprises a processor that acts upon data signals.
- 19. (Original) The system of claim 17, wherein the organic moieties comprise amide linkers.
- 20. (Original) The system of claim 17 wherein the organic moieties comprise thiol linkers.
- 21. (Original) The system of claim 17, wherein the organic moieties comprise amide linkers and thiol linkers.

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22. (Currently Amended) A process:

coating at least one surface of least one of a heat sink and of a die with a metal;

oxidizing carbon nanotubes ropes in sulfuric and nitric acids, whereby the carbon

nanotubes ropes are cut into a plurality of short carbon nanotubes with open ends having

carboxyl linkages attached thereto;

treating at least one end of at least some of a plurality of carbon nanotubes by applying

organic moieties thereto; and

tethering one end of the at least some of the carbon nanotubes of the plurality of carbon

nanotubes to the metal.

23. (Original) The process of claim 22 wherein the metal is selected from the group consisting

of gold and gold alloys.

24. (Original) The process of claim 23, wherein the treating the at least one end of some of the

plurality of nanotubes comprises forming an amide based linkage thereon.

25. (Original) The process of claim 23, wherein the treating the at least one end of some of the

plurality of nanotubes comprises forming an amide based linkage and a thiol based linkage

thereon.

26-30. (Canceled)